

Final Product Change Notification

202106009F01W

Issue Date: 23-Jul-2021
Effective Date: 24-Jul-2021

WITHDRAWAL

Here's your personalized quality information concerning products Digi-Key purchased from Nexperia.
 For More details Please Contact your respective Nexperia CSR/AM.



Change Category

- | | | | | |
|---|--|--|---|---|
| <input checked="" type="checkbox"/> Wafer Fab Process | <input type="checkbox"/> Assembly Process | <input type="checkbox"/> Product Marking | <input type="checkbox"/> Test Location | <input type="checkbox"/> Design |
| <input type="checkbox"/> Wafer Fab Materials | <input checked="" type="checkbox"/> Assembly Materials | <input type="checkbox"/> Mechanical Specification | <input type="checkbox"/> Test Process | <input type="checkbox"/> Errata |
| <input type="checkbox"/> Wafer Fab Location | <input type="checkbox"/> Assembly Location | <input type="checkbox"/> Packing/Shipping/Labeling | <input type="checkbox"/> Test Equipment | <input type="checkbox"/> Electrical spec./Test coverage |

Change of back side metallization thickness and introduction of new EMCs in SOT23

Details of this Change

WITHDRAWAL

- change of product list necessary
- remove PESD2ETH100-T and PESD2ETH1G-T from product list
- new PCN 202107006F01 with updated product list will be issued on short term

The back side metallization thickness will be changed from 2.15 µm to 1.75 µm.
 The change of the back side metallization thickness is combined with the introduction of additional EMCs (epoxy mold compounds) GR646CHN, CV4112 and E500HK.

Following the details:

Current Products

- back side metallization thickness 2.15 µm
- epoxy mold compound: GR646 (where affected) and E500HK (where affected)

Changed Products

- back side metallization thickness 1.75 µm
- epoxy mold compound: GR646 (where affected), CV4112 (where affected), E500HK and GR646CHN

Please find more information in the files linked below:

https://qcm.nexperia.com/change-notification-epcn/SQR_202106009F01.pdf

https://qcm.nexperia.com/change-notification-epcn/202106009F01_DeQuMa_PCN-Form.zip

Why do we Implement this Change

- to increase efficiency of volume production
- to increase flexibility and volume ramp-up

Identification of Affected Products

Changed product can be identified by date code after implementation.

Product Availability

Sample Information

Samples are available upon request

Latest sample request date for PCN samples is 08-Aug-2021.

Production

Planned first shipment 01-Nov-2021

Withdrawal Information

- change of product list necessary
- remove PESD2ETH100-T and PESD2ETH1G-T from product list
- new PCN 202107006F01 with updated product list will be issued on short term

Impact

No impact to the products' functionality anticipated.

Disposition of Old Products

Existing inventory will be shipped until depleted

Additional information

Timing and Logistics

Your acknowledgement of this change, conform JEDEC J-STD-046, is expected till 22-Aug-2021. Lack of acknowledgement of the PCN constitutes acceptance of the change.

Contact and Support

For all Quality Notification content inquiries, please contact your local Nexperia Sales Support team.

For specific questions on this notice or the products affected please contact our specialist directly:

e-mail address pcn@nexperia.com

In case of distribution, please contact your distribution partner.

At Nexperia B.V. we are constantly striving to improve our product and processes to ensure they reach the highest possible Quality Standards.

About Nexperia B.V.

We at Nexperia are the efficiency semiconductor company. We deliver over 90 billion products a year and as such service thousands of global customers, both directly and through our extensive network of channel partners. We are at the heart of billions of electronic devices in the Automotive, Mobile, Industrial, Consumer, Computing, and Communication Infrastructure segments.

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Nexperia |

Nexperia B.V.

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Changed Orderable Part#	Changed Part 12NC	Changed Part Number	Changed Part Description	Package Outline	Package Name	Status	Product Line
BC806-25VL	934661121235	BC806-25	80 V, 500 mA PNP general-purpose transistors	SOT23	TO-236AB	RFS	Bipolar Discretes
PESD2ETH100-TR	934661532215	PESD2ETH100-T	ESD protection for In-vehicle networks	SOT23	TO-236AB	RFS	Bipolar Discretes
BAS31,215	933723190215	BAS31	General purpose controlled avalanche (double) diod	SOT23	TO-236AB	RFS	Bipolar Discretes
BC806-25HR	934661591215	BC806-25H	80 V, 500 mA PNP general-purpose transistors	SOT23	TO-236AB	RFS	Bipolar Discretes
BC807-16LZ	934660115185	BC807-16L	45 V, 500 mA PNP general-purpose transistors	SOT23	TO-236AB	RFS	Bipolar Discretes
BAT721S,215	934054930215	BAT721S	40 V, 200 mA dual Schottky barrier diode	SOT23	TO-236AB	RFS	Bipolar Discretes
BC806-25HVL	934661591235	BC806-25H	80 V, 500 mA PNP general-purpose transistors	SOT23	TO-236AB	RFS	Bipolar Discretes
PBSS5130T,215	934057988215	PBSS5130T	30 V; 1 A PNP low VCEsat (BISS) transistor	SOT23	TO-236AB	RFS	Bipolar Discretes
BC807-25HR	934660829215	BC807-25H	45 V, 500 mA PNP general-purpose transistors	SOT23	TO-236AB	RFS	Bipolar Discretes
BC807-16HVL	934660828235	BC807-16H	45 V, 500 mA PNP general-purpose transistors	SOT23	TO-236AB	RFS	Bipolar Discretes
PESD5VOS2BT,215	934058007215	PESD5VOS2BT	Low capacitance bidirectional double ESD protectio	SOT23	TO-236AB	RFS	Bipolar Discretes
PBSS4320T,215	934056854215	PBSS4320T	20 V NPN low VCEsat transistor	SOT23	TO-236AB	RFS	Bipolar Discretes
BAT721,215	934051290215	BAT721	Schottky barrier single diode	SOT23	TO-236AB	RFS	Bipolar Discretes
PESD2ETH1G-TR	934661104215	PESD2ETH1G-T	ESD protection for In-vehicle networks	SOT23	TO-236AB	RFS	Bipolar Discretes
BC807-16HZ	934660828185	BC807-16H	45 V, 500 mA PNP general-purpose transistors	SOT23	TO-236AB	RFS	Bipolar Discretes
BC806-16VL	934661119235	BC806-16	80 V, 500 mA PNP general-purpose transistors	SOT23	TO-236AB	RFS	Bipolar Discretes
PBSS4230T,215	934057986215	PBSS4230T	30 V; 2 A NPN low VCEsat (BISS) transistor	SOT23	TO-236AB	RFS	Bipolar Discretes
BCX17,235	933209620235	BCX17	PNP general purpose transistors	SOT23	TO-236AB	RFS	Bipolar Discretes
BAT721A,215	934054928215	BAT721A	40 V, 200 mA Schottky barrier dual diode	SOT23	TO-236AB	RFS	Bipolar Discretes
BCW68HVL	934070946235	BCW68H	45 V, 800 mA PNP general-purpose transistor	SOT23	TO-236AB	RFS	Bipolar Discretes
BAS29,215	933723180215	BAS29	General purpose controlled avalanche (double) diod	SOT23	TO-236AB	RFS	Bipolar Discretes
BC806-16R	934661119215	BC806-16	80 V, 500 mA PNP general-purpose transistors	SOT23	TO-236AB	RFS	Bipolar Discretes
BC807-16HR	934660828215	BC807-16H	45 V, 500 mA PNP general-purpose transistors	SOT23	TO-236AB	RFS	Bipolar Discretes
PDTD114ETR	934031040215	PDTD114ET	500 mA, 50 V NPN resistor-equipped transistors	SOT23	TO-236AB	RFS	Bipolar Discretes
BAT721A,235	934054928235	BAT721A	40 V, 200 mA Schottky barrier dual diode	SOT23	TO-236AB	RFS	Bipolar Discretes
BC806-25R	934661121215	BC806-25	80 V, 500 mA PNP general-purpose transistors	SOT23	TO-236AB	RFS	Bipolar Discretes
PMMT491A,215	934055113215	PMMT491A	NPN BISS transistor	SOT23	TO-236AB	RFS	Bipolar Discretes
BCX17,215	933209620215	BCX17	PNP general purpose transistors	SOT23	TO-236AB	RFS	Bipolar Discretes
BC807-40HR	934660831215	BC807-40H	45 V, 500 mA PNP general-purpose transistors	SOT23	TO-236AB	RFS	Bipolar Discretes
BC807-40HVL	934660831235	BC807-40H	45 V, 500 mA PNP general-purpose transistors	SOT23	TO-236AB	RFS	Bipolar Discretes
2PD602AQL,215	934062311215	2PD602AQL	50 V, 500 mA NPN general-purpose transistors	SOT23	TO-236AB	RFS	Bipolar Discretes
PMMT591A,215	934055114215	PMMT591A	PNP BISS transistor	SOT23	TO-236AB	RFS	Bipolar Discretes
PBSS4120T,215	934057984215	PBSS4120T	20 V; 1 A NPN low VCEsat (BISS) transistor	SOT23	TO-236AB	RFS	Bipolar Discretes
BC807-40LVL	934660117235	BC807-40L	45 V, 500 mA PNP general-purpose transistors	SOT23	TO-236AB	RFS	Bipolar Discretes
BC807-25HZ	934660829185	BC807-25H	45 V, 500 mA PNP general-purpose transistors	SOT23	TO-236AB	RFS	Bipolar Discretes
BC807-40HZ	934660831185	BC807-40H	45 V, 500 mA PNP general-purpose transistors	SOT23	TO-236AB	RFS	Bipolar Discretes
PBSS5120T,215	934057987215	PBSS5120T	20 V; 1 A PNP low VCEsat (BISS) transistor	SOT23	TO-236AB	RFS	Bipolar Discretes
PBSS4130T,215	934057985215	PBSS4130T	30 V; 1 A NPN low VCEsat (BISS) transistor	SOT23	TO-236AB	RFS	Bipolar Discretes
BC807-25HVL	934660829235	BC807-25H	45 V, 500 mA PNP general-purpose transistors	SOT23	TO-236AB	RFS	Bipolar Discretes
2PB710ARL,215	934062302215	2PB710ARL	50 V, 500 mA PNP general-purpose transistors	SOT23	TO-236AB	RFS	Bipolar Discretes
BAT721C,215	934054929215	BAT721C	40 V, 200 mA, dual Schottky barrier diode	SOT23	TO-236AB	RFS	Bipolar Discretes